



US 20240213340A1

(19) **United States**

(12) **Patent Application Publication**
MORE et al.

(10) **Pub. No.: US 2024/0213340 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **SOURCE/DRAIN STRUCTURE FOR SEMICONDUCTOR DEVICE**

Publication Classification

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(51) **Int. Cl.**
H01L 29/417 (2006.01)
H01L 21/8234 (2006.01)
H01L 29/04 (2006.01)
H01L 29/66 (2006.01)
H01L 29/78 (2006.01)

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(52) **U.S. Cl.**
CPC *H01L 29/41791* (2013.01); *H01L 21/823418* (2013.01); *H01L 21/823431* (2013.01); *H01L 21/823475* (2013.01); *H01L 29/04* (2013.01); *H01L 29/66795* (2013.01); *H01L 29/785* (2013.01)

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(21) Appl. No.: **18/599,779**

(22) Filed: **Mar. 8, 2024**

Related U.S. Application Data

(63) Continuation of application No. 17/868,462, filed on Jul. 19, 2022, now Pat. No. 11,948,988, which is a continuation of application No. 16/935,890, filed on Jul. 22, 2020, now Pat. No. 11,469,305.

(57) **ABSTRACT**

The present disclosure describes a semiconductor structure and a method for forming the same. The semiconductor structure can include a substrate, a gate structure over the substrate, and a source/drain (S/D) region adjacent to the gate structure. The S/D region can include first and second side surfaces separated from each other. The S/D region can further include top and bottom surfaces between the first and second side surfaces. A first separation between the top and bottom surfaces can be greater than a second separation between the first and second side surfaces.

